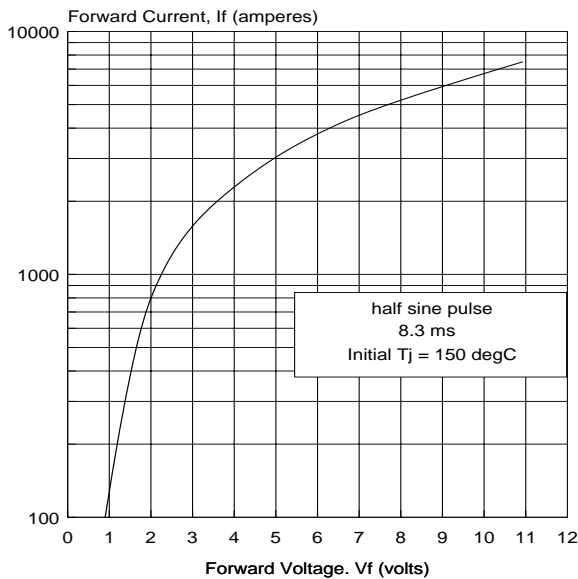


The SDD66 rectifier diode features a nominal 40mm silicon junction diameter design, manufactured by the proven multi-diffusion process. High reverse voltage blocking capability is optimized with moderate recovery current and low forward voltage.

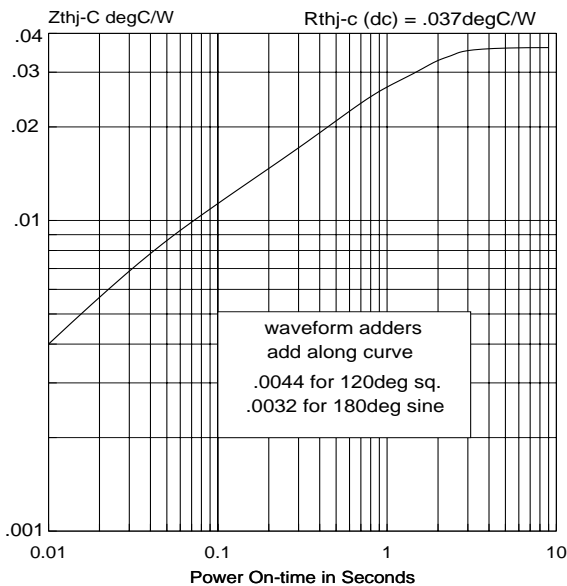
SDD66 is designed specifically for transportation, industrial and utility 50/60 Hz rectifiers having very high current surge and I<sup>2</sup>t requirements.

**FORWARD CHARACTERISTIC**  
Process Maximum



96h:t66 2/13/97

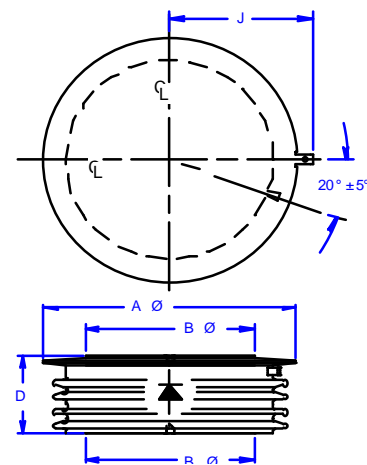
**THERMAL IMPEDANCE vs> POWER ON-TIME**



**SELECTION TABLE**

Model No.	Repetitive Peak Reverse Voltage $V_{RRM} @ T_J = 0 - 150^\circ C$	$V_{RRM} @ T_J = -40^\circ C$
SDD66MT	7000 V	6500 V
SDD66MR	6800	6300
SDD66MM	6600	6100
SDD66MH	6400	6000
SDD66MD	6200	5800
SDD66KT	6000	5600

**MECHANICAL OUTLINE**



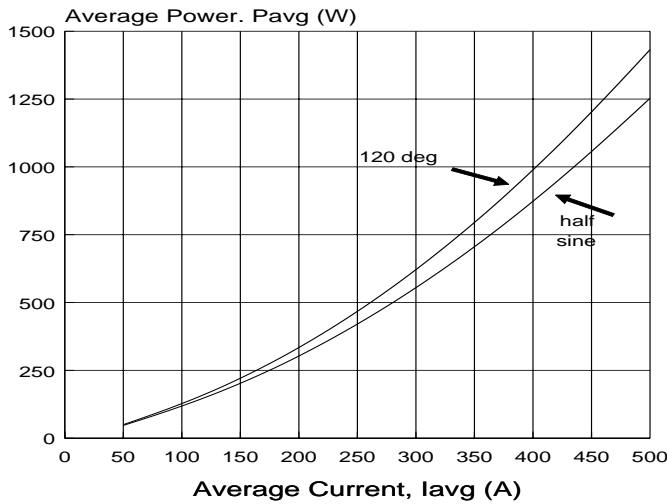
**A Ø = 2.30 in (58.0 mm)**  
**B Ø = 1.35 in (34.3 mm)**  
**D = 1.04 in (26.4 mm)**

**CLAMPING FORCE REQUIRED**  
3500 - 4200 lbs. 15.6 - 18.7kN

**LIMITING CHARACTERISTICS AND RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	MAX. VALUES	UNITS
Average current	$I_{AV}$	half sine $T_c = 10^\circ\text{C}$	520	A
Repetitive peak reverse voltage	$V_{RRM}$	$T_J = -40$ to $+150^\circ\text{C}$ 50/60 Hz	see page 1	V
Repetitive peak reverse current	$I_{RRM}$	$T_J = 150^\circ\text{C}$ 25°C	65 10	ma
Forward voltage	$V_{FM}$	$I_F = 1\text{kA}$ , $150^\circ\text{C}$	2.20	V
Peak recovery current	$I_{RM}$	$T_J = 150^\circ\text{C}$ @ 10A/us	250	A
Non-rep peak surge current	$I_{FSM}$	$T_J = 160^\circ$ $t_p = 8.3\text{ms}$ $t_p = 10\text{ms}$ $V_F = 0$	7500 7100	A

**POWER DISSIPATION**  
Full Cycle Average 50/60 Hz

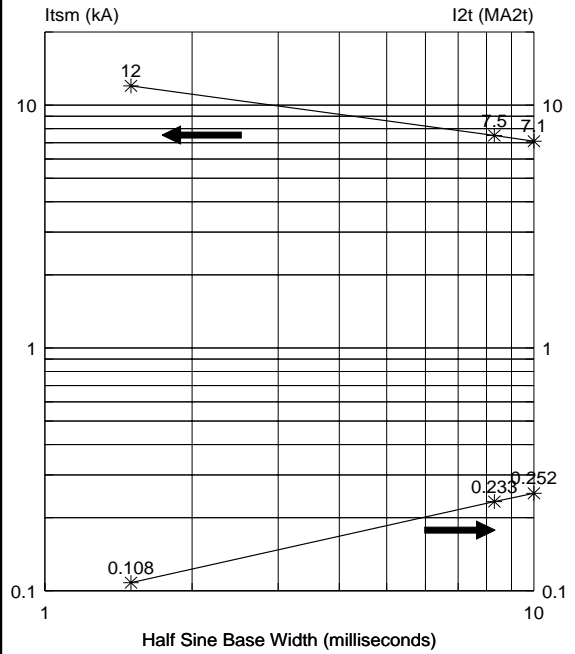


**AVERAGE POWER DISSIPATION**

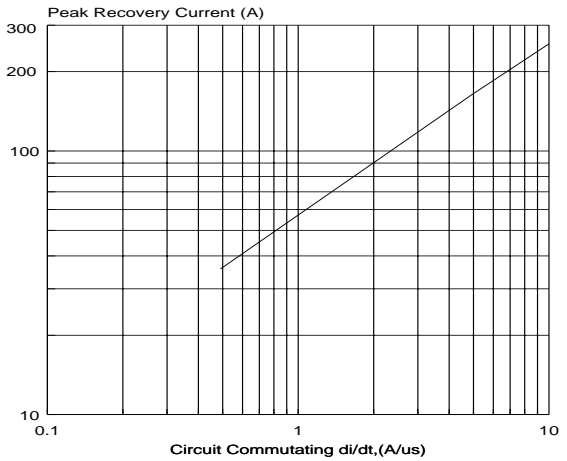
$T_j = 150 \text{ degC}$

$I_{AV}$ (A)	half sine	120° sq.
50	47	50
100	115	123
150	199	217
200	300	331
250	418	464
300	552	618
350	703	792
400	870	985
450	1053	1198
500	1253	1432

**NON-REPETITIVE SURGE CURRENT AND  $I_2t$  CAPABILITY FOR FUSE COORDINATION**



**MAXIMUM PEAK RECOVERY CURRENT**



SDD66